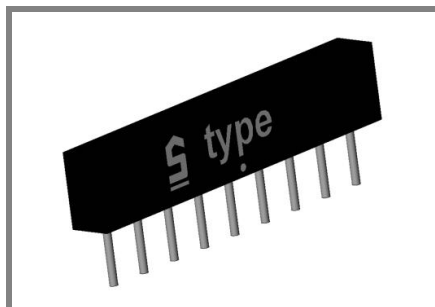


# DAN 801, DAP 801 (200mW) ...



## Diode arrays

## Silicon rectifiers arrays

### DAN 801, DAP 801 (200mW)

Forward Current: 0,1 A

Reverse Voltage: 80 to / V

Publish Data

### Features

### Mechanical Data

- 9 Pin - plastic case
- Terminals: plated terminals solderable per IEC 68-2-20
- Mounting position : any
- Weigh approx. 0,6 g
- Standard packing : bulk
- DAP 801 - common anodes
- DAN 801- common cathodes
- <sup>1)</sup> Valid for one branch; per diode for simultaneous operation  $I_{FAV} = 25 \text{ mA}$
- <sup>2)</sup>  $I_F = 10\text{mA}$ ,  $T_A = 25^\circ\text{C}$

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	$V_{RRM}$ V	$V_{RSM}$ V	$I_F = 10 \text{ m A}$ $I_R = 10 \text{ m A}$ $I_{RR} = 1 \text{ m A}$ $t_{rr}$ ns	$V_F^{2)}$
DAN 803	80	80	4	1,0
DAP 803	80	80	4	1,0

### Absolute Maximum Ratings

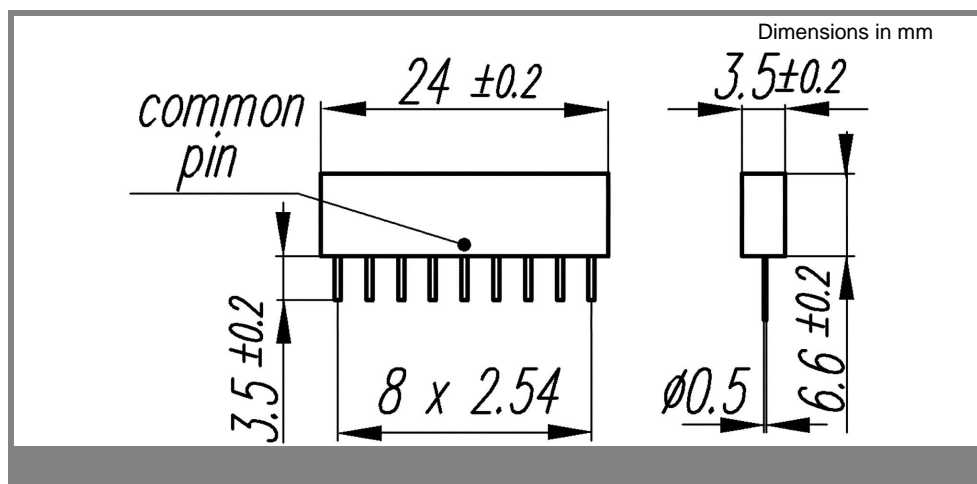
$T_C = 25^\circ\text{C}$  unless otherwise specified

Symbol	Conditions	Values	Units
$I_{FAV}$	Max. averaged fwd. current, R-load, $T_A = 25^\circ\text{C}$ <sup>1)</sup>	0,1	A
$I_{FRM}$	Repetitive peak forward current $f > 15 \text{ Hz}$ <sup>1)</sup>	0,2	A
$I_{FSM}$	Peak forward surge current 50 Hz half sinus-wave <sup>3)</sup>	0,5	A
$i^2t$	Rating for fusing, $t < 10 \text{ ms}$ <sup>3)</sup>	0,0012	$\text{A}^2\text{s}$
$R_{thA}$	Max. thermal resistance junction to ambient <sup>1)</sup>	85	K/W
$R_{thT}$	Max. thermal resistance junction to terminals <sup>1)</sup>	/	K/W
$T_j$	Operating junction temperature	-50 ... +150	$^\circ\text{C}$
$T_s$	Storage temperature	-50 ... +150	$^\circ\text{C}$

### Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise specified

Symbol	Conditions	Values	Units
$I_R$	Maximum leakage current, $T_j = 25^\circ\text{C}$ ; $V_R = V_{RRM}$	$< 25$ ( note : $V_R = 20 \text{ V}$ )	nA
	$T_j = ^\circ\text{C}$ ; $V_R = V_{RRM}$		
$C_j$	Typical junction capacitance (at MHz and applied reverse voltage of V)	/	pF
$Q_{rr}$	Reverse recovery charge ( $U_R = V$ ; $I_F = A$ ; $di_F/dt = A/\text{ms}$ )	/	$\mu\text{C}$
$E_{RSM}$	Non repetitive peak reverse avalanche energy ( $I_R = \text{mA}$ ; $T_j = ^\circ\text{C}$ ; inductive load switched off)		mJ



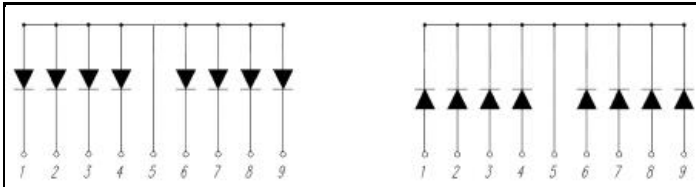


Fig. 1 : DAP 801 (Com. anodes) DAP 803 (Com. cathodes)